

General Purpose Transistors

NPN Silicon

BC846ALT1G Series

Features

- Moisture Sensitivity Level: 1
- ESD Rating – Human Body Model: > 4000 V
– Machine Model: > 400 V
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

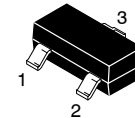
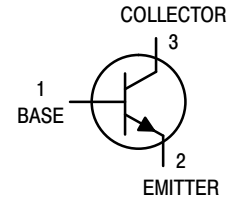
Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC846 BC847, BC850 BC848, BC849	V_{CEO}	65 45 30	Vdc
Collector-Base Voltage BC846 BC847, BC850 BC848, BC849	V_{CBO}	80 50 30	Vdc
Emitter-Base Voltage BC846 BC847, BC850 BC848, BC849	V_{EBO}	6.0 6.0 5.0	Vdc
Collector Current – Continuous	I_C	100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

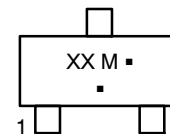
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.



SOT-23
CASE 318
STYLE 6

MARKING DIAGRAM



XX = Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 12.

BC846ALT1G Series

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage ($I_C = 10\text{ mA}$)	$V_{(BR)CEO}$	65 45 30	– – –	– – –	V
Collector – Emitter Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$, $V_{EB} = 0$)	$V_{(BR)CES}$	80 50 30	– – –	– – –	V
Collector – Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$)	$V_{(BR)CBO}$	80 50 30	– – –	– – –	V
Emitter – Base Breakdown Voltage ($I_E = 1.0\text{ }\mu\text{A}$)	$V_{(BR)EBO}$	6.0 6.0 5.0	– – –	– – –	V
Collector Cutoff Current ($V_{CB} = 30\text{ V}$) ($V_{CB} = 30\text{ V}$, $T_A = 150^\circ\text{C}$)	I_{CBO}	– –	– –	15 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5.0\text{ V}$)	h_{FE}	– – –	90 150 270	– – –	–
($I_C = 2.0\text{ mA}$, $V_{CE} = 5.0\text{ V}$)		110 200 420	180 290 520	220 450 800	
Collector – Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$) ($I_C = 100\text{ mA}$, $I_B = 5.0\text{ mA}$)	$V_{CE(sat)}$	– –	– –	0.25 0.6	V
Base – Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$) ($I_C = 100\text{ mA}$, $I_B = 5.0\text{ mA}$)	$V_{BE(sat)}$	– –	0.7 0.9	– –	V
Base – Emitter Voltage ($I_C = 2.0\text{ mA}$, $V_{CE} = 5.0\text{ V}$) ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ V}$)	$V_{BE(on)}$	580 –	660 –	700 770	mV
SMALL – SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	–	–	MHz
Output Capacitance ($V_{CB} = 10\text{ V}$, $f = 1.0\text{ MHz}$)	C_{obo}	–	–	4.5	pF
Noise Figure ($I_C = 0.2\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	NF	– –	– –	10 4.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BC846ALT1G Series

BC846A, BC847A, BC848A, SBC846A

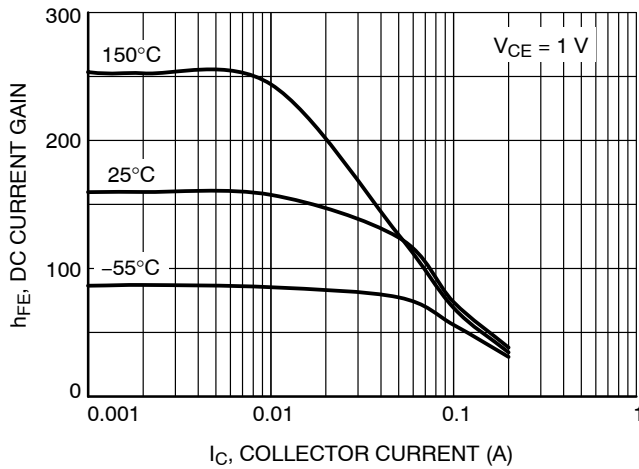


Figure 1. DC Current Gain vs. Collector Current

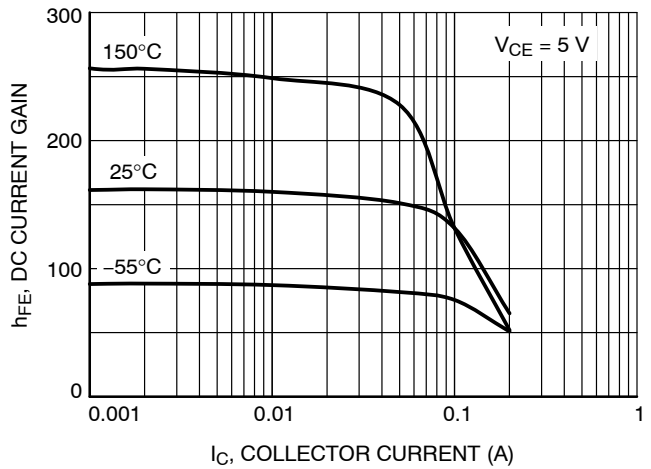


Figure 2. DC Current Gain vs. Collector Current

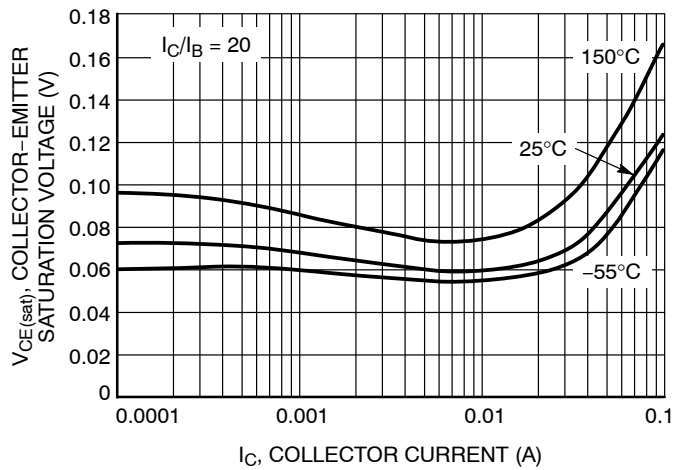


Figure 3. Collector Emitter Saturation Voltage vs. Collector Current

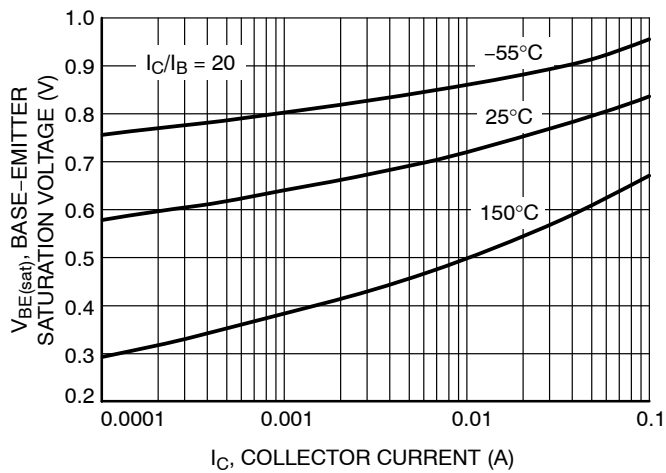


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

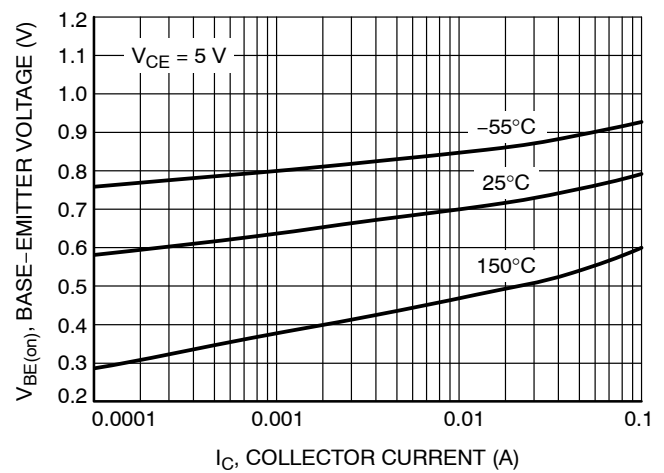


Figure 5. Base Emitter Voltage vs. Collector Current

BC846ALT1G Series

BC846A, BC847A, BC848A, SBC846A

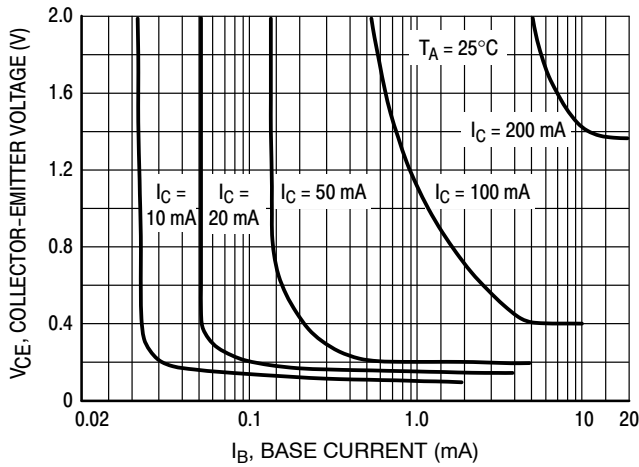


Figure 6. Collector Saturation Region

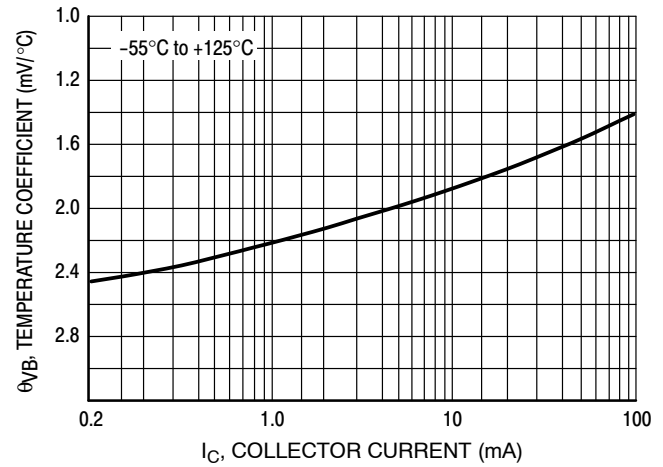


Figure 7. Base-Emitter Temperature Coefficient

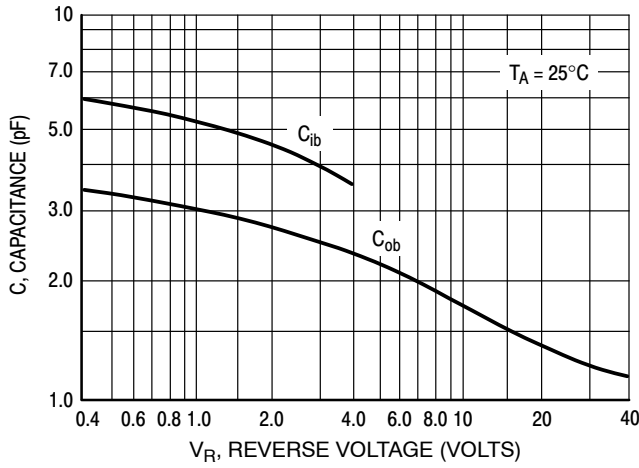


Figure 8. Capacitances

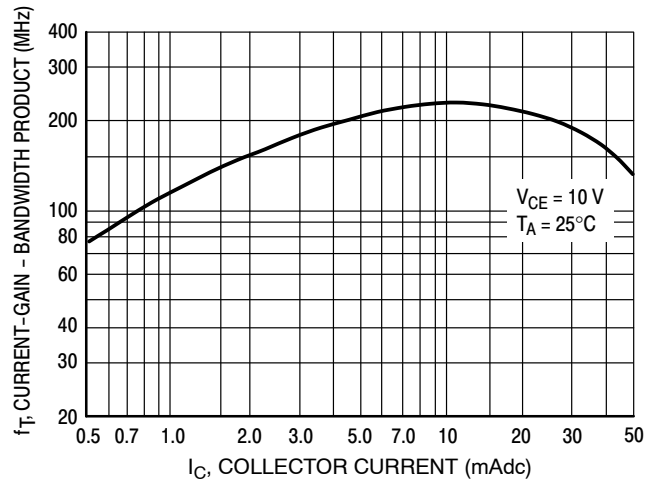


Figure 9. Current-Gain - Bandwidth Product

BC846ALT1G Series

BC846B, SBC846B

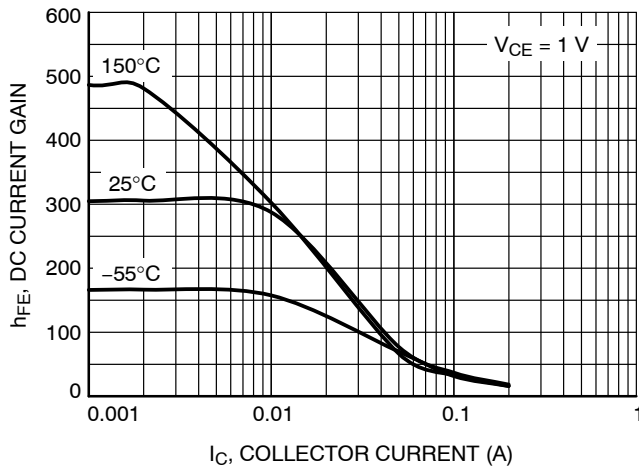


Figure 10. DC Current Gain vs. Collector Current

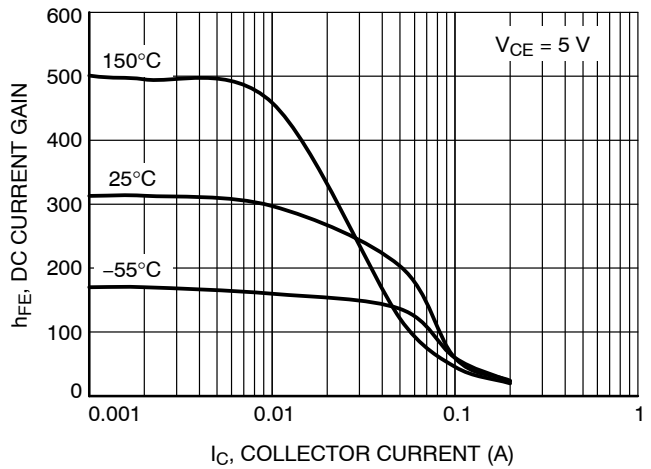


Figure 11. DC Current Gain vs. Collector Current

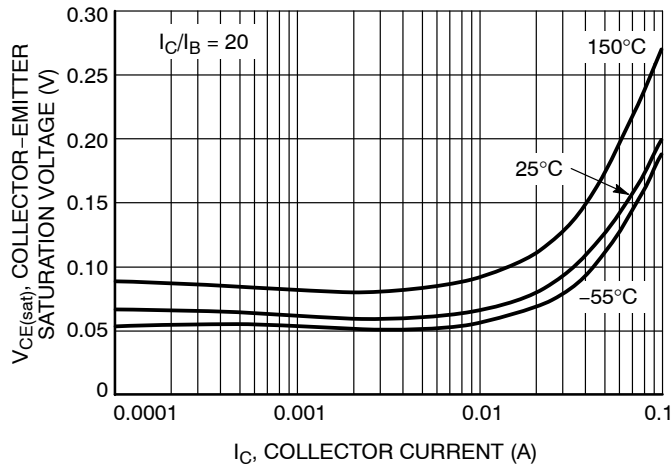


Figure 12. Collector-Emitter Saturation Voltage vs. Collector Current

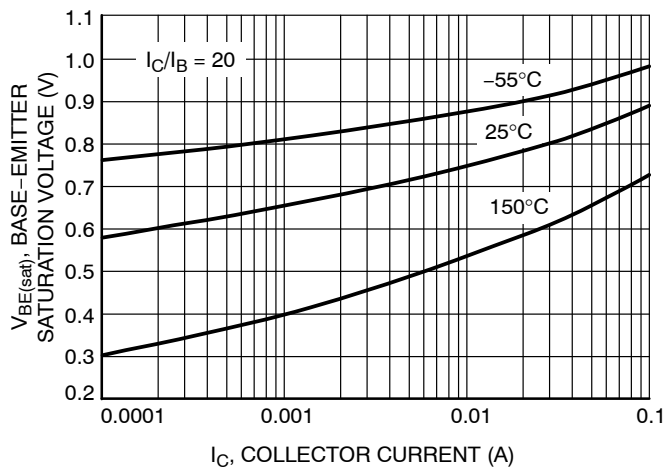


Figure 13. Base-Emitter Saturation Voltage vs. Collector Current

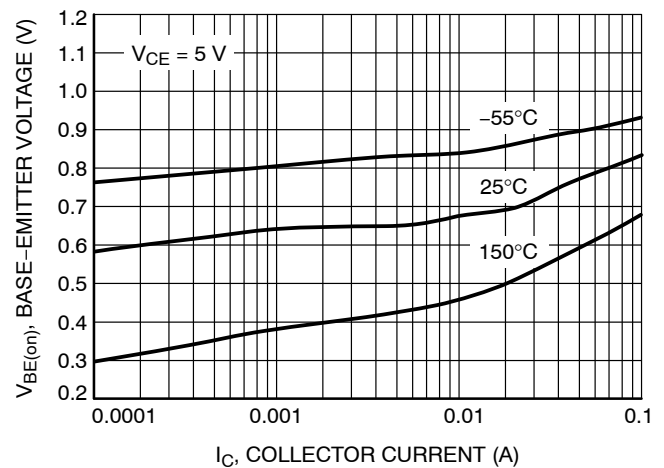


Figure 14. Base-Emitter Voltage vs. Collector Current

BC846ALT1G Series

BC846B, SBC846B

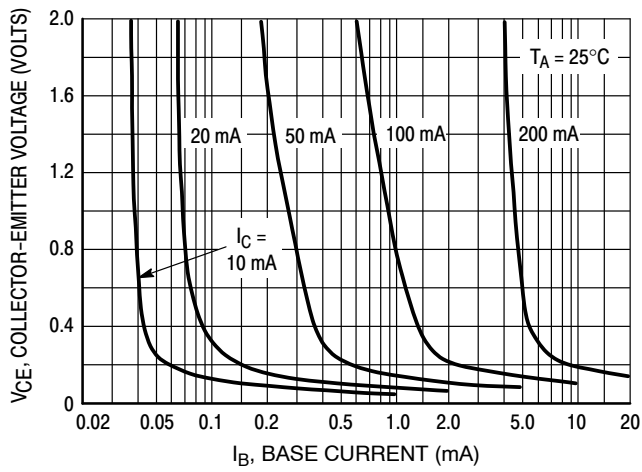


Figure 15. Collector Saturation Region

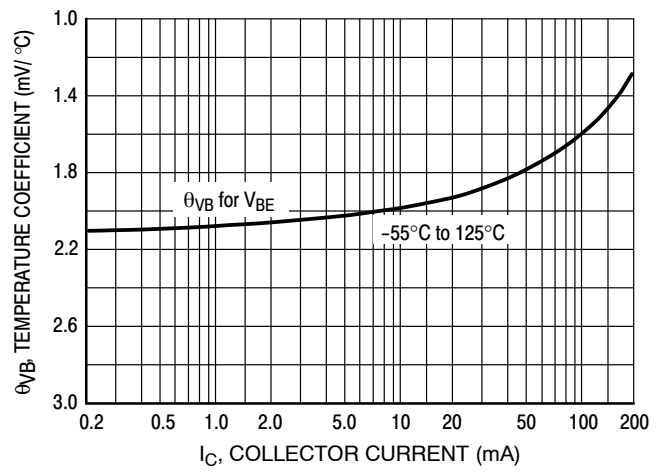


Figure 16. Base-Emitter Temperature Coefficient

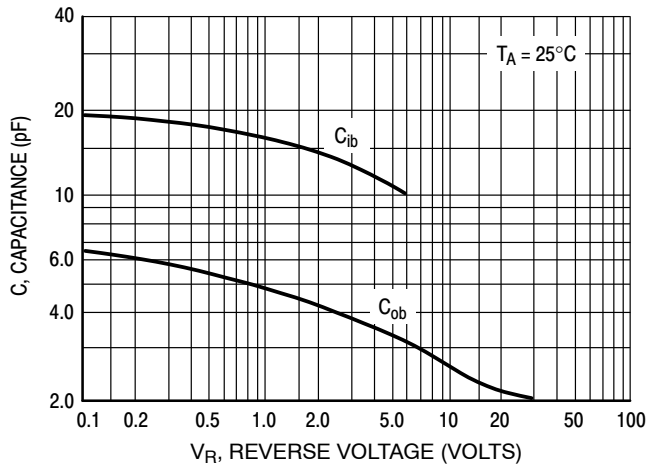


Figure 17. Capacitance

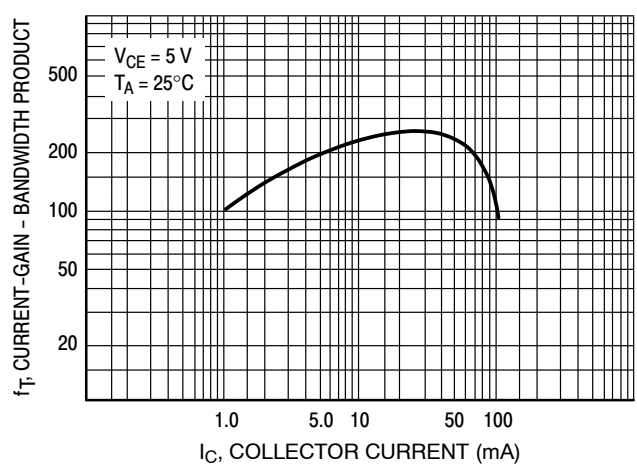


Figure 18. Current-Gain - Bandwidth Product

BC846ALT1G Series

BC847B, BC848B, BC849B, BC850B, SBC847B, SBC848B

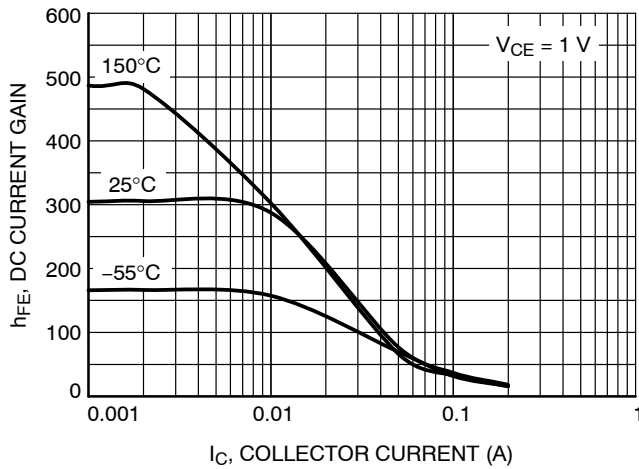


Figure 19. DC Current Gain vs. Collector Current

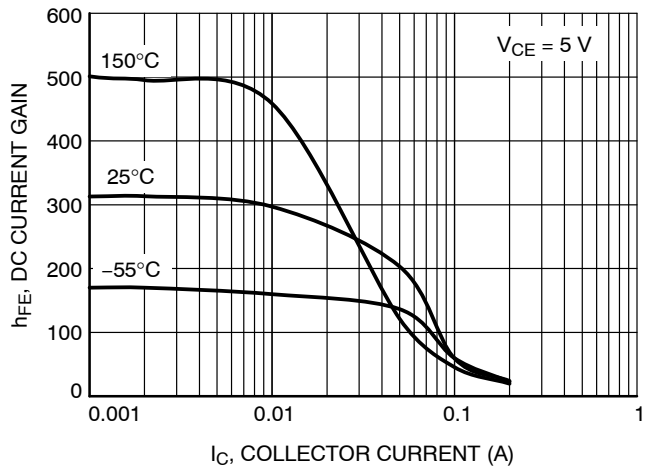


Figure 20. DC Current Gain vs. Collector Current

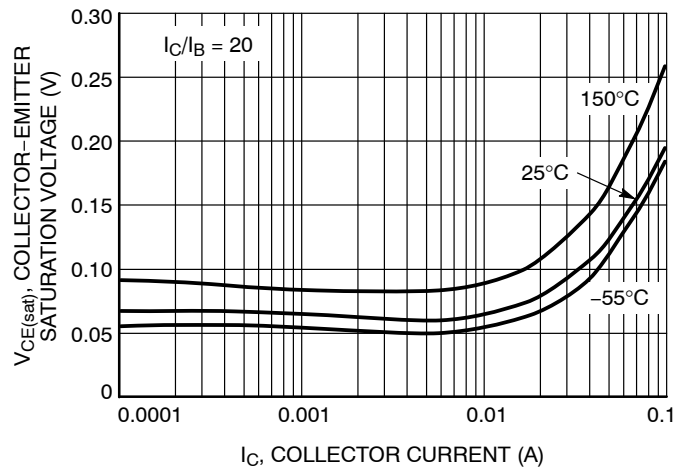


Figure 21. Collector Emitter Saturation Voltage vs. Collector Current

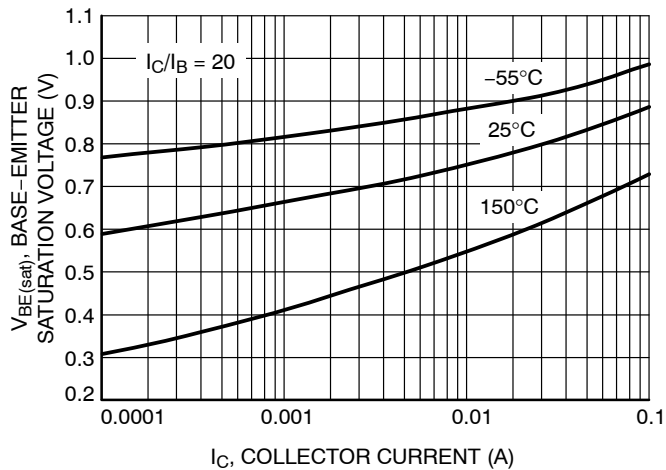


Figure 22. Base Emitter Saturation Voltage vs. Collector Current

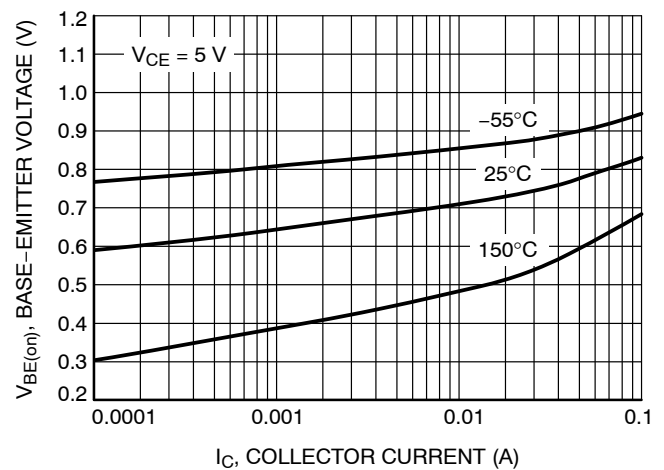


Figure 23. Base Emitter Voltage vs. Collector Current

BC846ALT1G Series

BC847B, BC848B, BC849B, BC850B, SBC846B, SBC847B, SBC848B

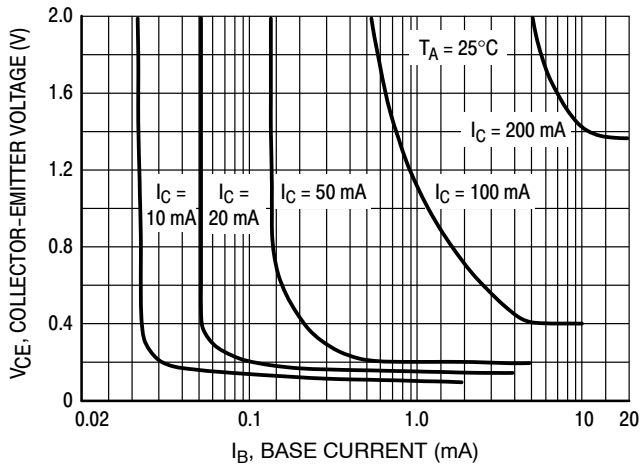


Figure 24. Collector Saturation Region

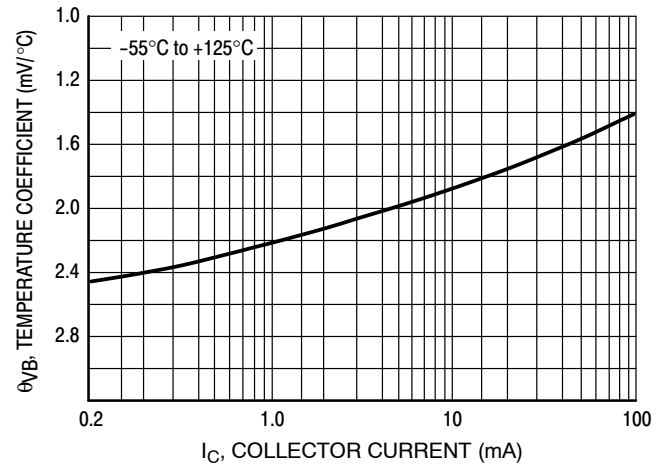


Figure 25. Base-Emitter Temperature Coefficient

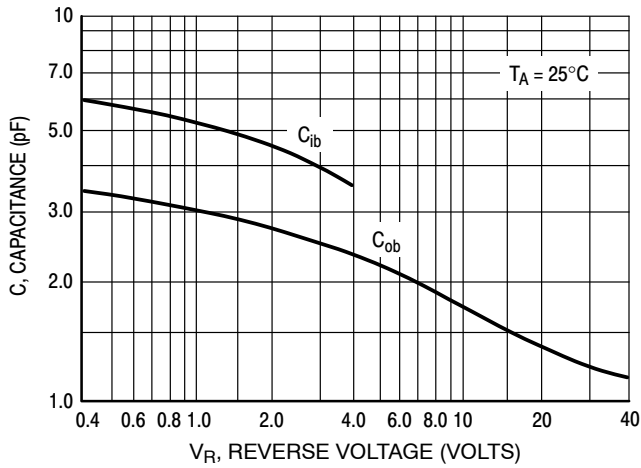


Figure 26. Capacitances

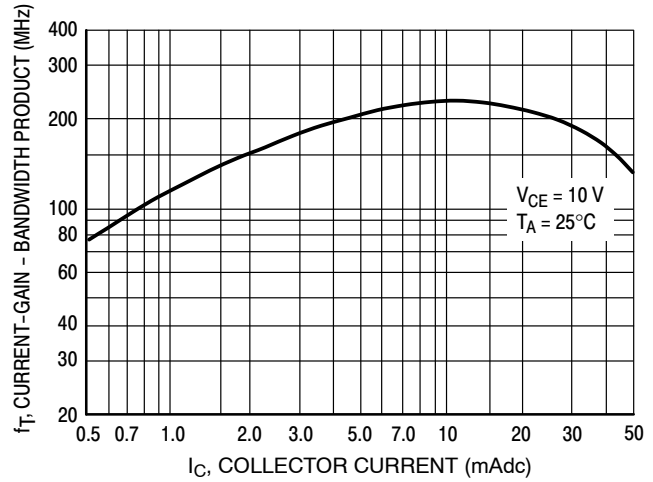


Figure 27. Current-Gain - Bandwidth Product

BC846ALT1G Series

BC846C, BC847C, BC848C, BC849C, BC850C, SBC847C

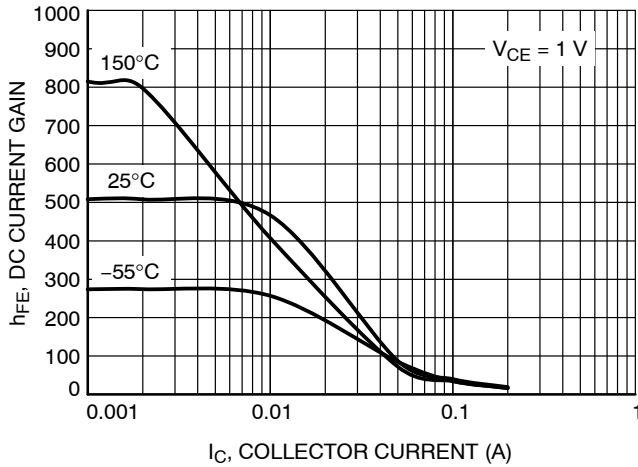


Figure 28. DC Current Gain vs. Collector Current

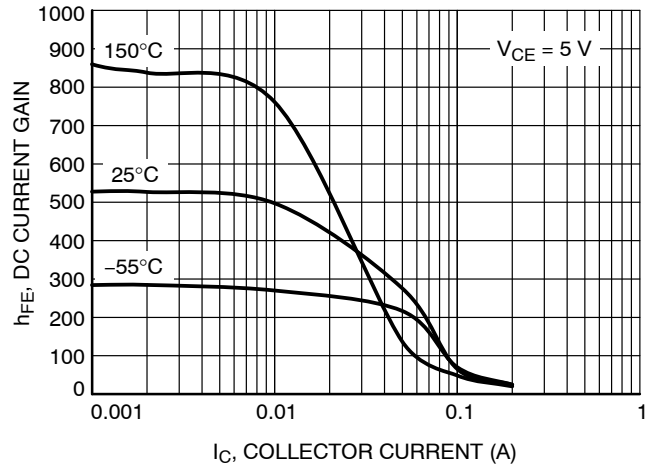


Figure 29. DC Current Gain vs. Collector Current

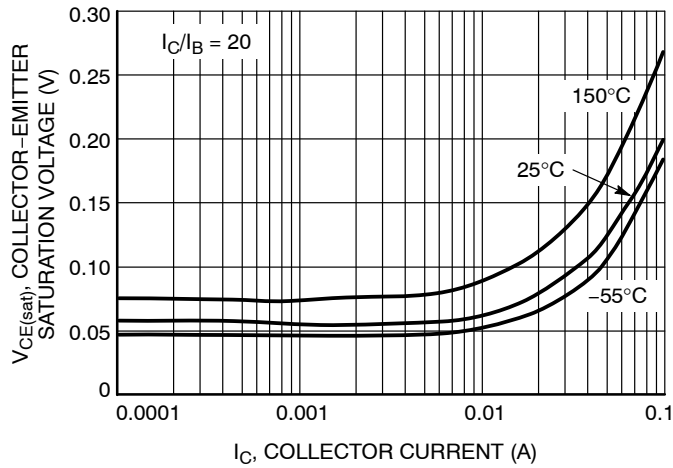


Figure 30. Collector-Emitter Saturation Voltage vs. Collector Current

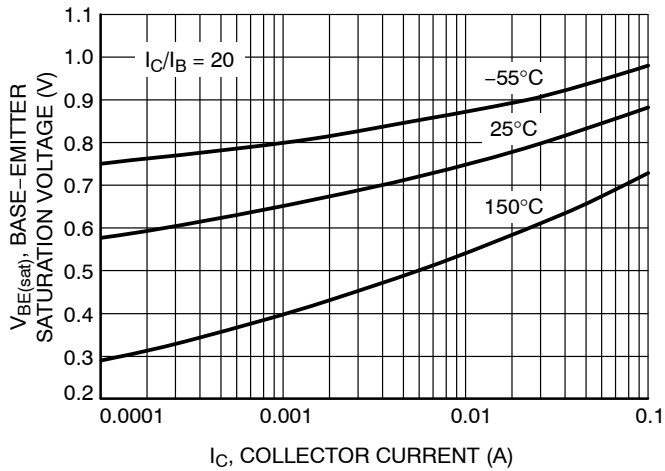


Figure 31. Base-Emitter Saturation Voltage vs. Collector Current

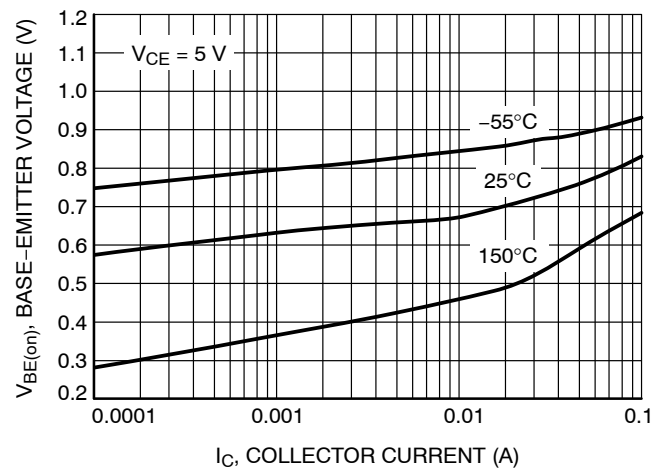


Figure 32. Base-Emitter Voltage vs. Collector Current

BC846ALT1G Series

BC846C, BC847C, BC848C, BC849C, BC850C, SBC847C

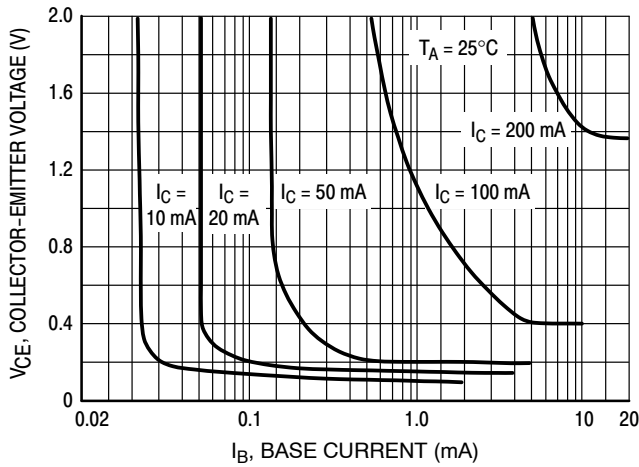


Figure 33. Collector Saturation Region

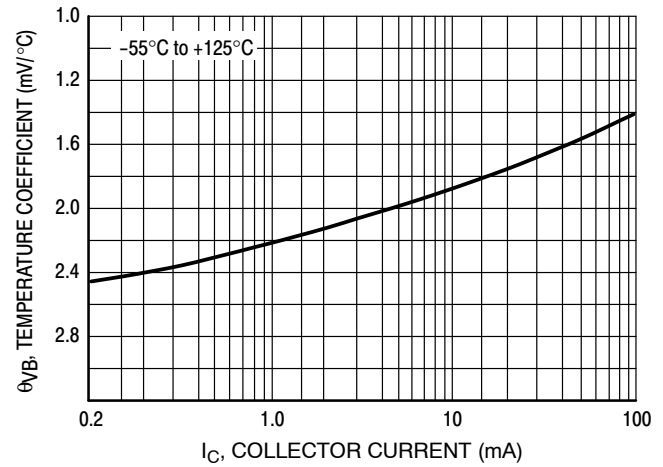


Figure 34. Base-Emitter Temperature Coefficient

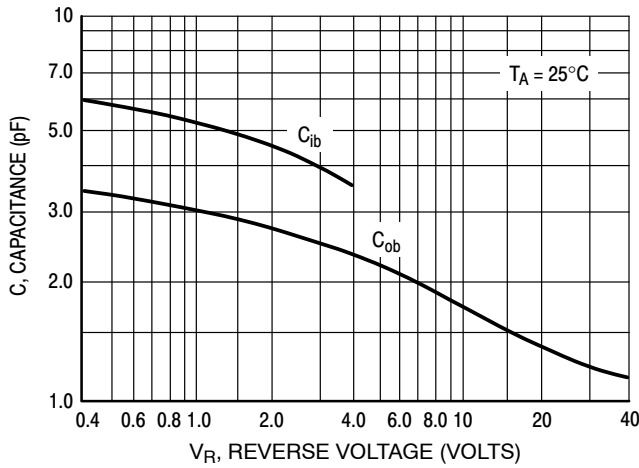


Figure 35. Capacitances

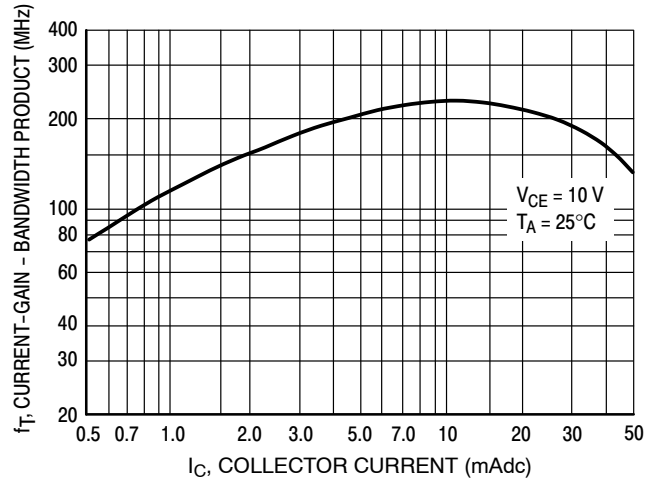
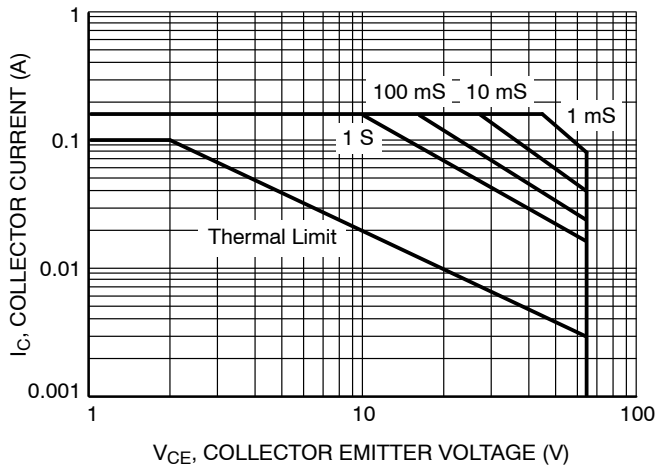
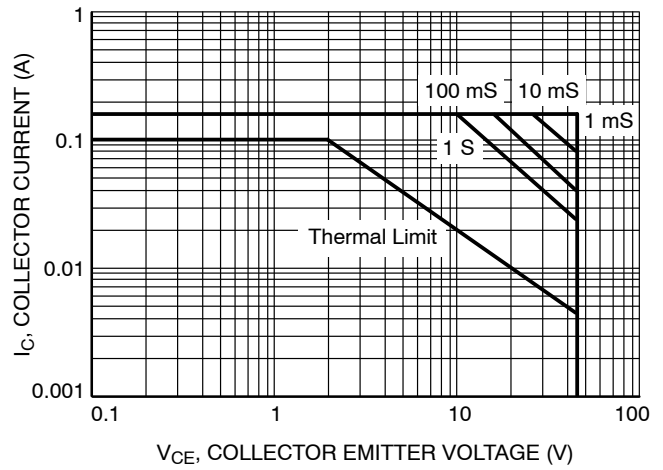


Figure 36. Current-Gain - Bandwidth Product

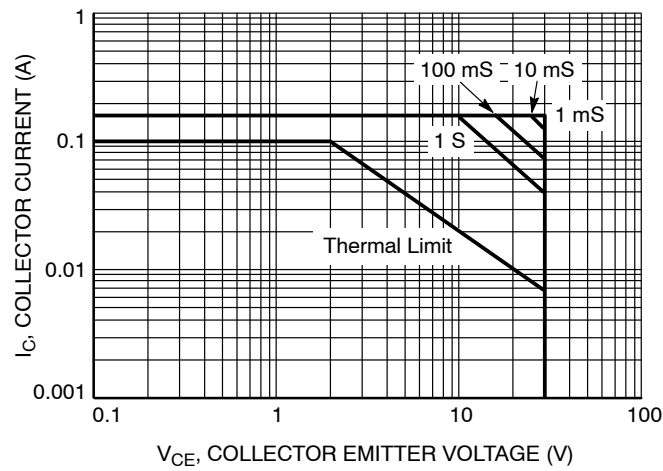
BC846ALT1G Series



**Figure 37. Safe Operating Area for
BC846A, BC846B, BC846C**



**Figure 38. Safe Operating Area for
BC847A, BC847B, BC847C, BC850B, BC850C**



**Figure 39. Safe Operating Area for
BC848A, BC848B, BC848C, BC849B, BC849C**

BC846ALT1G Series

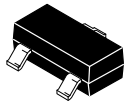
ORDERING INFORMATION

DISCONTINUED (Note 3)

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

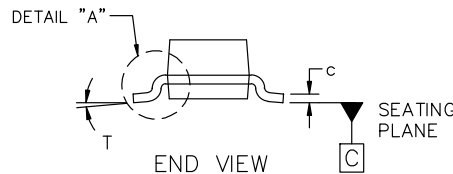
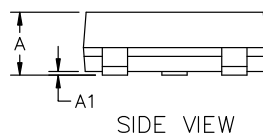
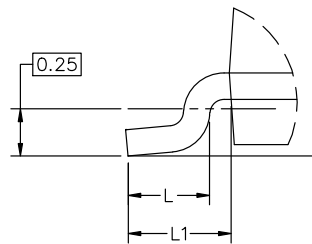
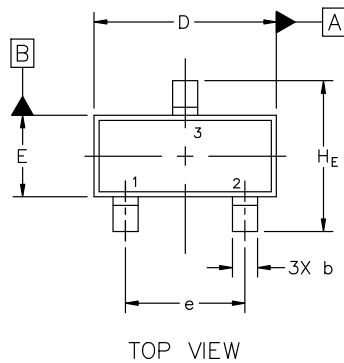
3. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

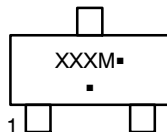


MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

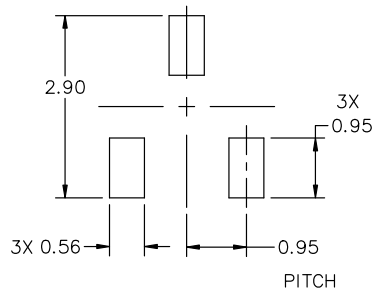
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P	PAGE 1 OF 2

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SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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